MOSFET - Power for 1-Cell Lithium-ion Battery Protection

EFC2K103NUZ 12 V, 1.8 mΩ, 40 A, Dual N-Channel

This power MOSFET features a low on-state resistance. This device is suitable for applications such as power switches of portable machines. Best suited for 1-cell lithium-ion battery applications.

Features

- 2.5 V drive
- Common–Drain type
- ESD Diode–Protected Gate
- Pb-Free, Halogen Free and RoHS Compliance

Typical Applications

• 1-Cell Lithium-ion Battery Charging and Discharging Switch

SPECIFICATIONS

ABSOLUTE MAXIMUM RATINGS at $T_A = 25^{\circ}C$

Parameter	Symbol	Value	Unit
Source to Source Voltage	V _{SSS}	12	V
Gate to Source Voltage	V _{GSS}	±8	V
Source Current (DC)	ا _S	40	А
Source Current (Pulse) PW \leq 10 μ S, Duty Cycle \leq 1%	I _{SP}	140	A
Total Dissipation (Note 1)	P _T	3.3	W
Junction Temperature	TJ	150	°C
Storage Temperature	T _{stg}	-55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL RESISTANCE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Junction to Ambient (Note 1)	$R_{ hetaJA}$	37	°C/W

1. Surface mounted on ceramic substrate (5000 $\text{mm}^2 \times 0.8 \text{ mm})$



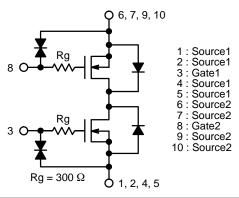
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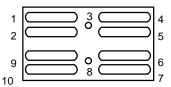
V _{SSS}	R _{SS(ON)} MAX	I _S MAX
12 V	1.8 mΩ @ 4.5 V	40 A
	1.9 mΩ @ 3.8 V	
	2.6 mΩ @ 3.1 V	
	4.2 mΩ @ 2.5 V	

ELECTRICAL CONNECTION

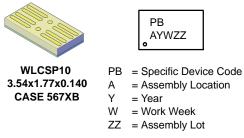
N-Channel







MARKING DIAGRAM



ORDERING INFORMATION

See detailed ordering, marking and shipping information in the package dimensions section on page 2 of this data sheet.

ELECTRICAL CHARACTERISTICS at $T_A = 25^{\circ}C$

				Value			
Parameter Symb		Conditions		Min	Тур	Max	Unit
Source to Source Breakdown Voltage	V _{(BR)SSS}	I_{S} = 1 mA, V_{GS} = 0 V	Test Circuit 1	12	-	-	V
Zero Gate Voltage Source Current	I _{SSS}	$V_{SS} = 10 \text{ V}, V_{GS} = 0 \text{ V}$	Test Circuit 1	-	-	1	μA
Gate to Source Leakage Current	I _{GSS}	$V_{GS} = \pm 8 \text{ V}, V_{SS} = 0 \text{ V}$	Test Circuit 2	-	-	±1	μΑ
Gate Threshold Voltage	V _{GS} (th)	$V_{SS} = 6 V, I_{S} = 1 mA$	Test Circuit 3	0.4	-	1.3	V
Static Source to Source On–State Resistance	R _{SS} (on)	$I_{\rm S}$ = 5 A, $V_{\rm GS}$ = 4.5 V	Test Circuit 4	0.8	1.25	1.8	mΩ
		$I_{S} = 5 \text{ A}, V_{GS} = 3.8 \text{ V}$	Test Circuit 4	0.85	1.35	1.9	mΩ
		$I_{\rm S} = 5$ A, $V_{\rm GS} = 3.1$ V	Test Circuit 4	1.0	1.7	2.6	mΩ
		I _S = 5 A, V _{GS} = 2.5 V	Test Circuit 4	1.2	2.1	4.2	mΩ
Turn–ON Delay Time	t _d (on)	V_{SS} = 6 V, V_{GS} = 3.8 V, I_S = 5 A, R_G = 10 $k\Omega$ Test Circuit 5		_	25	_	μs
Rise Time	t _r			-	100	-	μs
Turn-OFF Delay Time	t _d (off)			-	165	-	μs
Fall Time	t _f			-	148	-	μs
Total Gate Charge	Qg	$V_{SS} = 6 \text{ V}, V_{GS} = 3.8 \text{ V}, I_S$ Test Circuit 6	= 5 A	-	62	-	nC
Forward Source to Source Voltage	V _{F(S-S)}	$I_{S} = 3 \text{ A}, V_{GS} = 0 \text{ V}$	Test Circuit 7	_	0.75	1.2	V

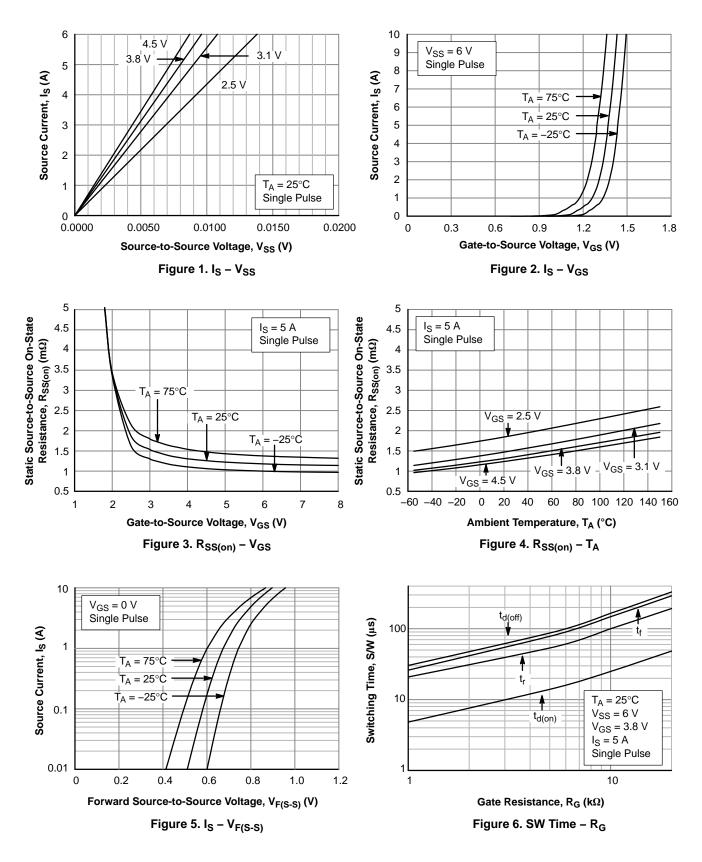
Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

ORDERING INFORMATION

Device	Device Marking Package		Shipping (Qty / Packing) [†]		
EFC2K103NUZTDG	PB	WLCSP10, $3.54 \times 1.77 \times 0.140$ (Pb-Free / Halogen Free)	5,000 / Tape & Reel		

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

TYPICAL CHARACTERISTICS



TYPICAL CHARACTERISTICS (Continued)

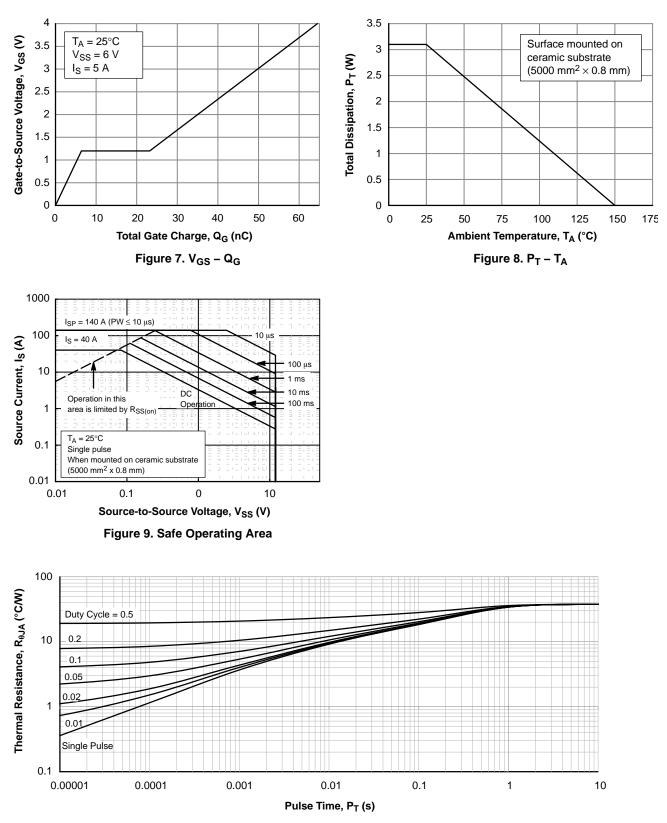
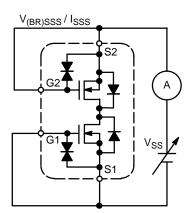
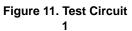


Figure 10. Thermal Response

TEST CIRCUITS ARE EXAMPLES OF MEASURING FET1 SIDE

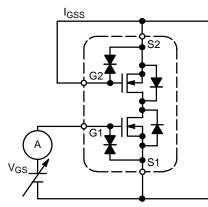




V_{GS}(th)

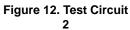
When FET1 is measured, Gate and Source of FET2 are short-circuited.

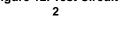
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When FET1 is measured, Gate and Source of FET2 are short-circuited.

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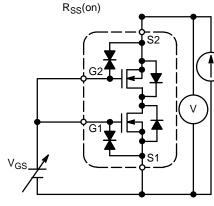
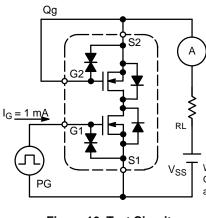
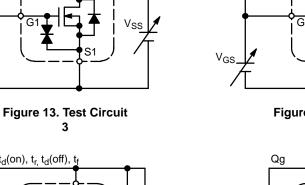


Figure 14. Test Circuit 4

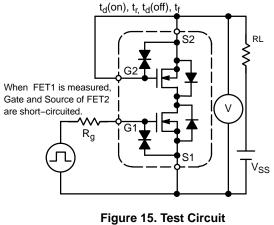


When FET1 is measured, Gate and Source of FET2 are short-circuited.

Figure 16. Test Circuit 6

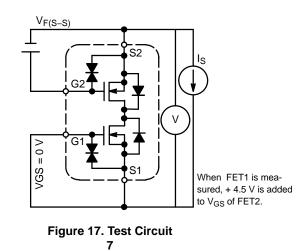


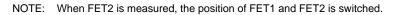
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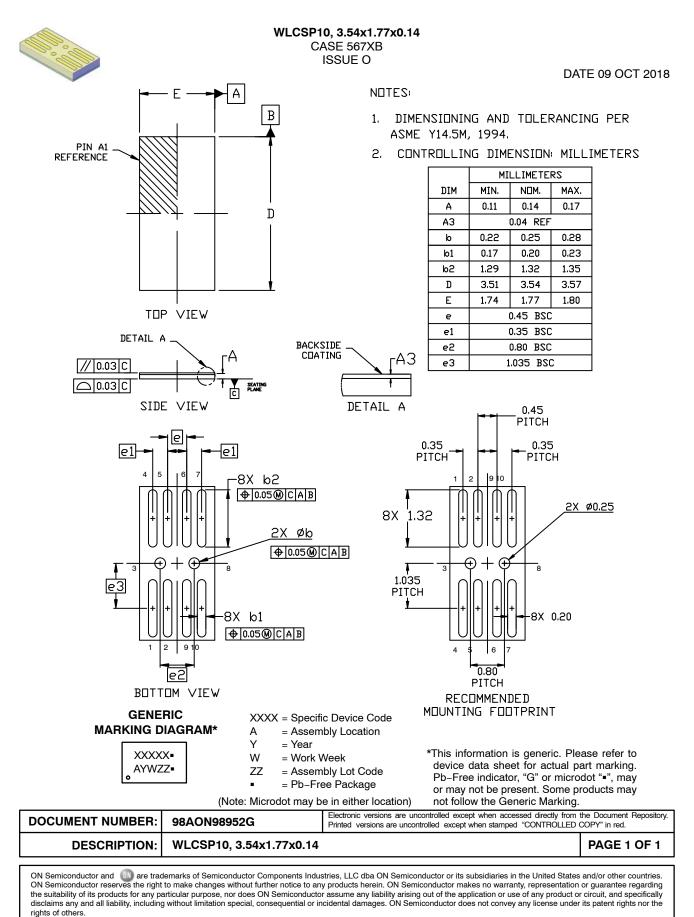






NOTE: Since the EFC2K103NUZ is a MOSFET product, please avoid using this device in the vicinity of highly charged objects. Please contact sales for use except the designated application.





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